

Product Summary

BV_{DSS}	Max R_{D(S)}	Max I_D @ T _A = 25°C
-30V	1Ω @ V _{GS} = -4.5V	-0.67A
	1.5Ω @ V _{GS} = -2.5V	-0.54A
	2Ω @ V _{GS} = -1.8V	-0.47A

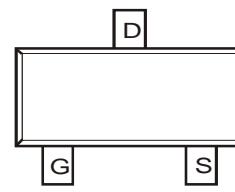
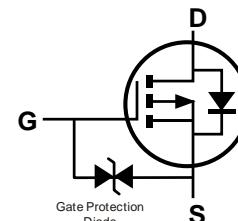
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{D(S)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Load Switch in Portable Electronics



Top View


 Top View
Internal Schematic


Equivalent Circuit

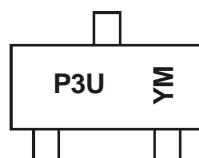
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP31D0U-7	SOT23	3,000/Tape & Reel

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

Marking Information



P3U = Product Type Marking Code

YM = Date Code Marking

Y = Year (ex: Y = 2011)

M = Month (ex: 9 = September)

Date Code Key

Year	2011	~	2016	2017	2018	2019	2020	2021	2022	2023		
Code	Y	~	D	E	F	G	H	I	J	K		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	± 8	V
Continuous Drain Current	Steady State	$T_A = +25^\circ\text{C}$ (Note 6) $T_A = +85^\circ\text{C}$ (Note 6) $T_A = +25^\circ\text{C}$ (Note 5)	I_D	-0.67 -0.48 -0.53	A
Pulsed Drain Current (Note 7)			I_{DM}	2.5	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	0.45	W
	(Note 6)		0.71	W
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	275	$^\circ\text{C}/\text{W}$
	(Note 6)		177	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes:
 5. Device mounted on FR-4 PCB, with minimum recommended pad layout
 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 7. Device mounted on minimum recommended pad layout test board, 10 μs pulse duty cycle = 1%.

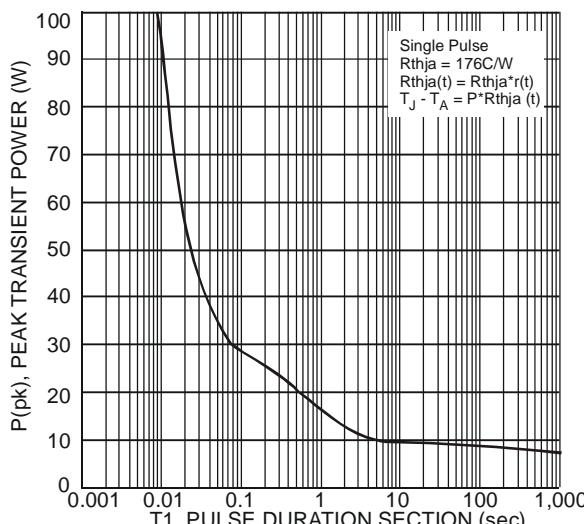


Fig. 1 Single Maximum Power Dissipation

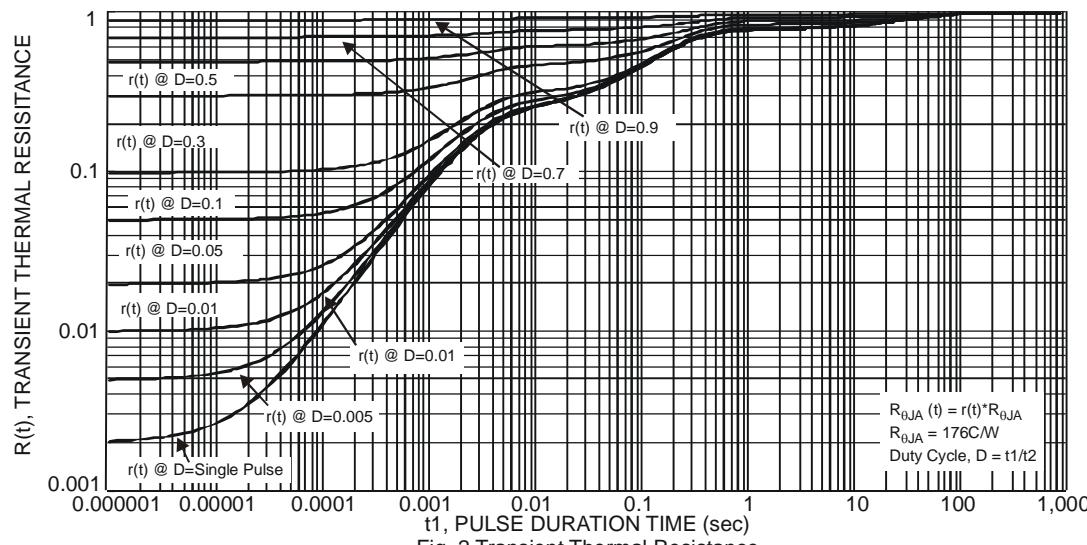


Fig. 2 Transient Thermal Resistance

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	$V_{\text{GS}} = 0\text{V}$, $I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = 25^\circ\text{C}$	I_{DSS}	—	—	-1	μA	$V_{\text{DS}} = -30\text{V}$, $V_{\text{GS}} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 3	μA	$V_{\text{GS}} = \pm 8\text{V}$, $V_{\text{DS}} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{\text{GS(TH)}}$	-0.5	—	-1.1	V	$V_{\text{DS}} = V_{\text{GS}}$, $I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{\text{DS}}(\text{ON})$	—	—	1	Ω	$V_{\text{GS}} = -4.5\text{V}$, $I_D = -400\text{mA}$
				1.5		$V_{\text{GS}} = -2.5\text{V}$, $I_D = -200\text{mA}$
				2		$V_{\text{GS}} = -1.8\text{V}$, $I_D = -100\text{mA}$
Forward Transfer Admittance	$ Y_{\text{FS}} $	50	—	—	mS	$V_{\text{DS}} = -3\text{V}$, $I_D = -300\text{mA}$
Diode Forward Voltage	V_{SD}	—	—	-1.2	V	$V_{\text{GS}} = 0\text{V}$, $I_S = -300\text{mA}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{ISS}	—	76	150	pF	$V_{\text{DS}} = -15\text{V}$, $V_{\text{GS}} = 0\text{V}$, $f = 1.0\text{MHz}$
Output Capacitance	C_{OSS}	—	9	—	pF	
Reverse Transfer Capacitance	C_{RSS}	—	6.43	—	pF	$V_{\text{GS}} = -4.5\text{V}$, $V_{\text{DS}} = -15\text{V}$, $I_D = -1\text{A}$
Gate Resistance	R_G	—	167	—	Ω	
Total Gate Charge	Q_G	—	0.9	—	nC	$V_{\text{GS}} = -8\text{V}$, $V_{\text{DS}} = -15\text{V}$, $I_D = -1\text{A}$
Total Gate Charge	Q_G	—	1.5	—	nC	
Gate-Source Charge	Q_{GS}	—	0.1	—	nC	$V_{\text{DD}} = -10\text{V}$, $R_L = 10\Omega$
Gate-Drain Charge	Q_{GD}	—	0.2	—	nC	
Turn-On Delay Time	$t_{\text{D(ON)}}$	—	5.0	—	ns	$V_{\text{GS}} = -4.5\text{V}$, $R_G = 6\Omega$
Turn-On Rise Time	t_R	—	5.9	—	ns	
Turn-Off Delay Time	$t_{\text{D(OFF)}}$	—	35.7	—	ns	$V_{\text{GS}} = -4.5\text{V}$, $R_G = 6\Omega$
Turn-Off Fall Time	t_F	—	16.7	—	ns	

Notes: 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.

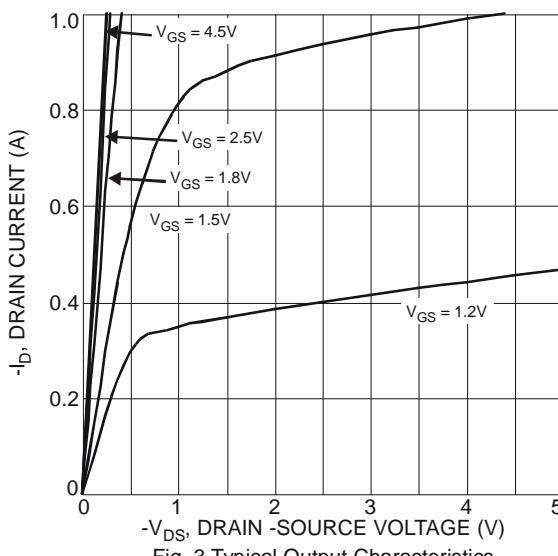
Typical Electrical Characteristics


Fig. 3 Typical Output Characteristics

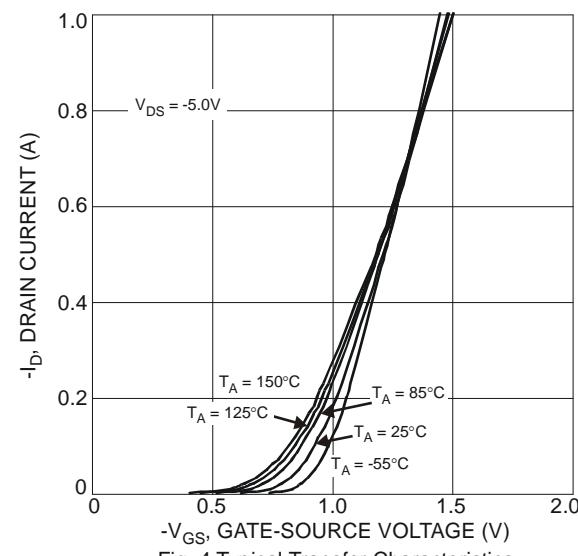


Fig. 4 Typical Transfer Characteristics

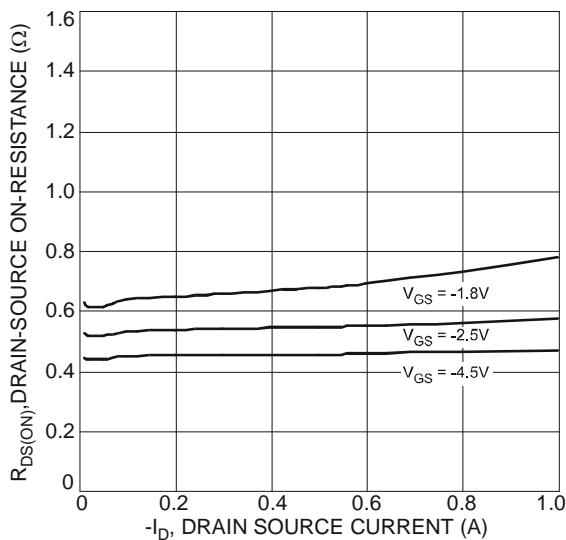


Fig. 5 Typical On-Resistance vs.
Drain Current and Gate Voltage

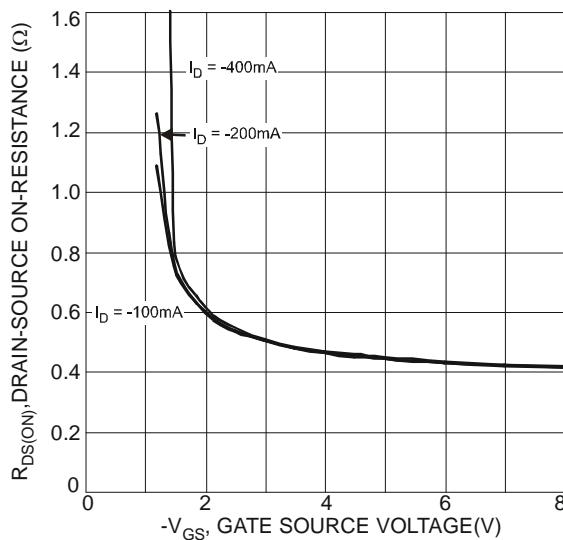


Fig. 6 Typical On-Resistance vs.
Drain Current and Gate Voltage

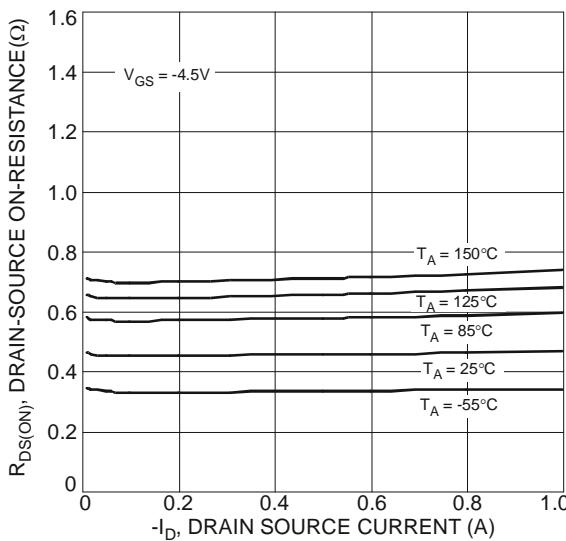


Fig. 7 Typical On-Resistance vs.
Drain Current and Temperature

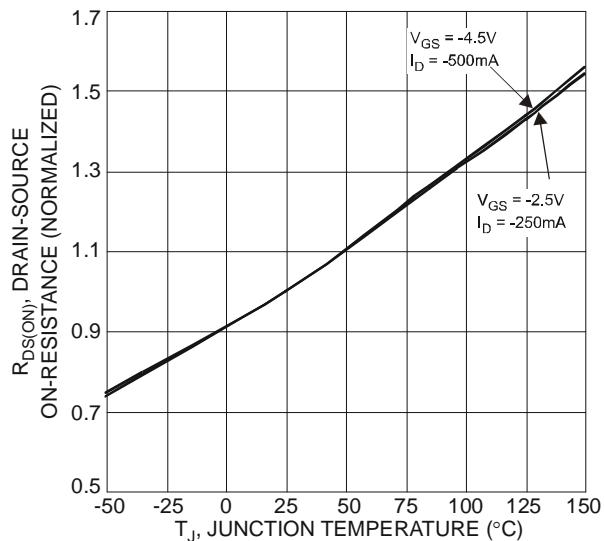


Fig. 8 On-Resistance Variation with Temperature

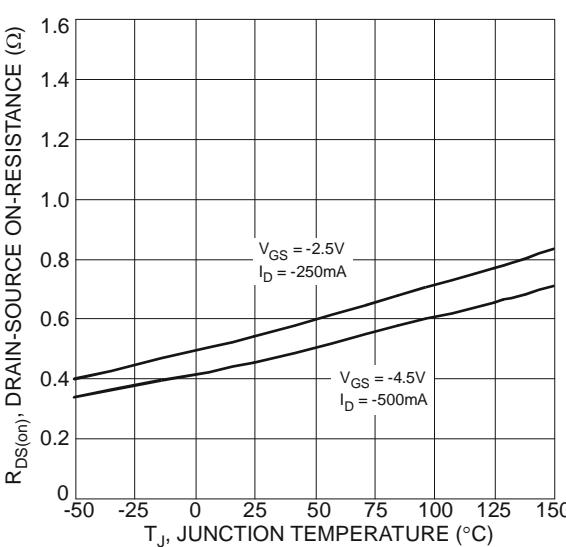


Fig. 9 On-Resistance Variation with Temperature

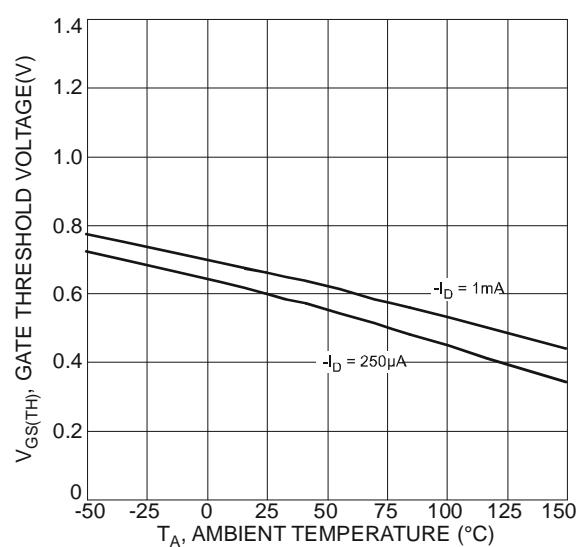


Fig. 10 Gate Threshold Variation vs. Ambient Temperature

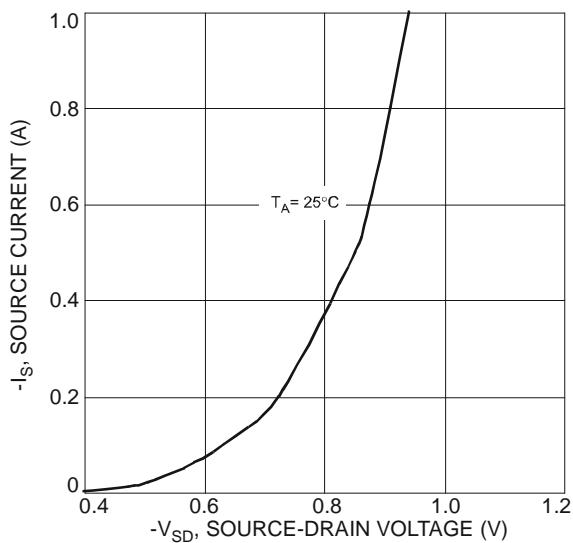


Fig. 11 Diode Forward Voltage vs. Current

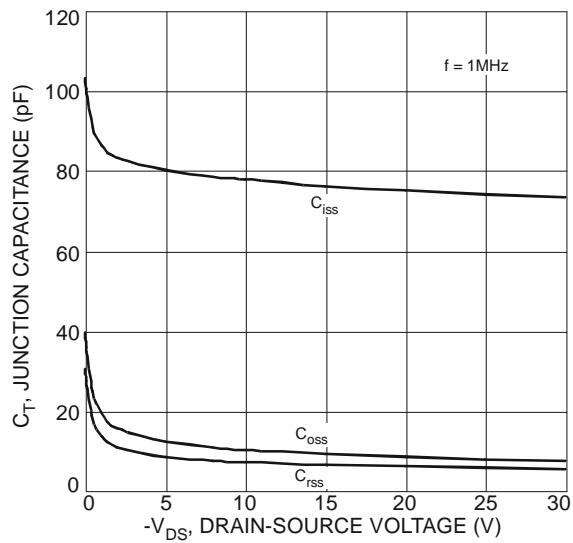


Fig. 12 Typical Junction Capacitance

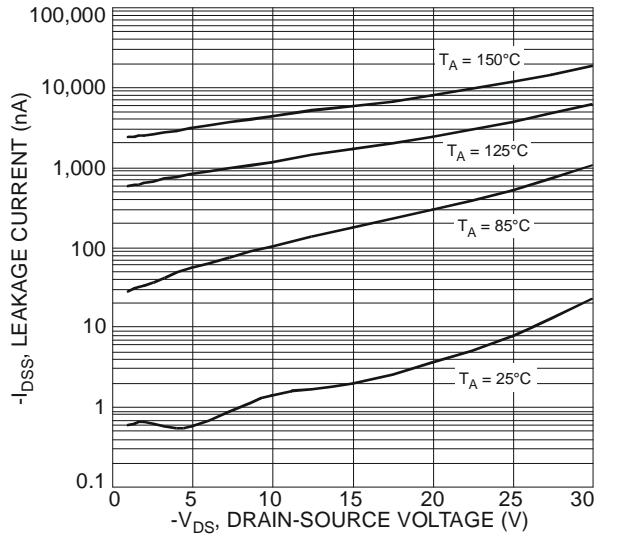


Fig. 13 Typical Drain-Source Leakage Current vs. Voltage

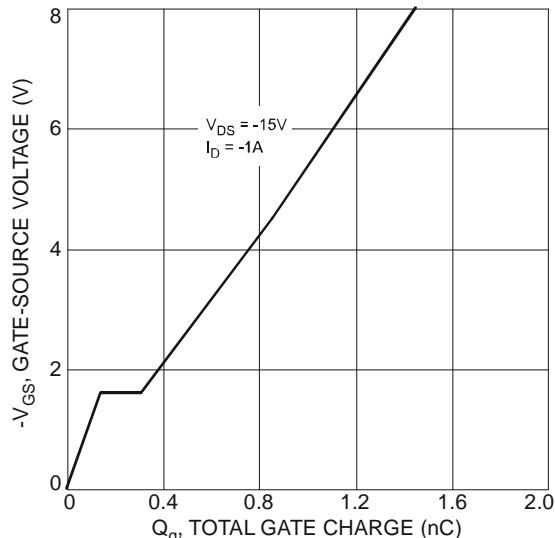
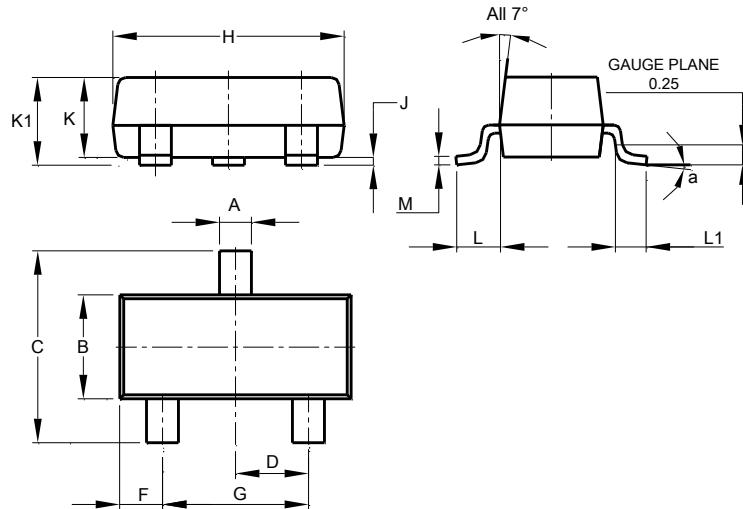


Fig. 14 Gate-Charge Characteristics

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



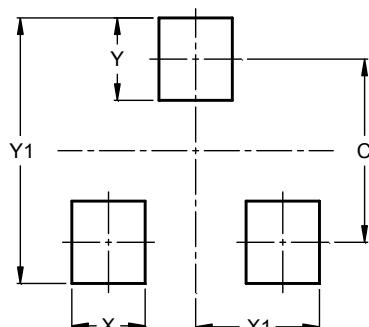
SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	—

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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